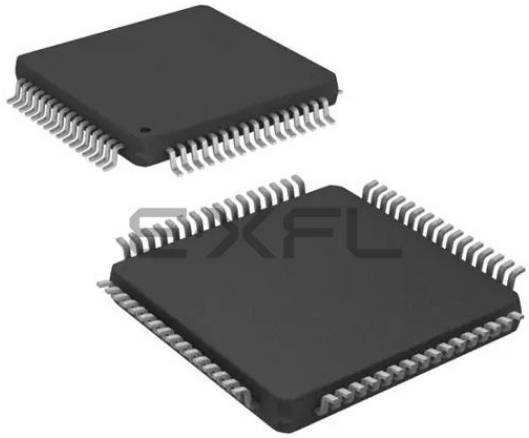

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	AVR
Core Size	8/16-Bit
Speed	32MHz
Connectivity	I²C, IrDA, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, POR, PWM, WDT
Number of I/O	50
Program Memory Size	192KB (96K x 16)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 3.6V
Data Converters	A/D 16x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	64-TQFP
Supplier Device Package	64-TQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/atxmega192d3-an

7.7 I/O Memory

The status and configuration registers for peripherals and modules, including the CPU, are addressable through I/O memory locations. All I/O locations can be accessed by the load (LD/LDS/LDD) and store (ST/STS/STD) instructions, which are used to transfer data between the 32 registers in the register file and the I/O memory. The IN and OUT instructions can address I/O memory locations in the range of 0x00 to 0x3F directly. In the address range 0x00 - 0x1F, single-cycle instructions for manipulation and checking of individual bits are available.

The I/O memory address for all peripherals and modules is shown in the “Peripheral Module Address Map” on page 55.

7.7.1 General Purpose I/O Registers

The lowest 16 I/O memory addresses are reserved as general purpose I/O registers. These registers can be used for storing global variables and flags, as they are directly bit-accessible using the SBI, CBI, SBIS, and SBIC instructions.

7.8 Memory Timing

Read and write access to the I/O memory takes one CPU clock cycle. A write to SRAM takes one cycle, and a read from SRAM takes two cycles. EEPROM page load (write) takes one cycle, and three cycles are required for read. For burst read, new data are available every second cycle. Refer to the instruction summary for more details on instructions and instruction timing.

7.9 Device ID and Revision

Each device has a three-byte device ID. This ID identifies Atmel as the manufacturer of the device and the device type. A separate register contains the revision number of the device.

7.10 I/O Memory Protection

Some features in the device are regarded as critical for safety in some applications. Due to this, it is possible to lock the I/O register related to the clock system, the event system, and the advanced waveform extensions. As long as the lock is enabled, all related I/O registers are locked and they can not be written from the application software. The lock registers themselves are protected by the configuration change protection mechanism.

7.11 Flash and EEPROM Page Size

The flash program memory and EEPROM data memory are organized in pages. The pages are word accessible for the flash and byte accessible for the EEPROM.

Table 7-2 on page 18 shows the Flash Program Memory organization and Program Counter (PC) size. Flash write and erase operations are performed on one page at a time, while reading the Flash is done one byte at a time. For Flash access the Z-pointer (Z[m:n]) is used for addressing. The most significant bits in the address (FPAGE) give the page number and the least significant address bits (FWORD) give the word in the page.

32. Electrical Characteristics

All typical values are measured at T = 25°C unless other temperature condition is given. All minimum and maximum values are valid across operating temperature and voltage unless other conditions are given.

32.1 Atmel ATxmega32D3

32.1.1 Absolute Maximum Ratings

Stresses beyond those listed in Table 32-1 may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Table 32-1. Absolute Maximum Ratings

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
V_{CC}	Power supply voltage		-0.3		4	V
I_{VCC}	Current into a V_{CC} pin				200	mA
I_{GND}	Current out of a Gnd pin				200	
V_{PIN}	Pin voltage with respect to Gnd and V_{CC}		-0.5		V_{CC} + 0.5	V
I_{PIN}	I/O pin sink/source current		-25		25	mA
T_A	Storage temperature		-65		150	°C
T_j	Junction temperature				150	

32.1.2 General Operating Ratings

The device must operate within the ratings listed in Table 32-31 on page 82 in order for all other electrical characteristics and typical characteristics of the device to be valid.

Table 32-2. General Operating Conditions

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
V_{CC}	Power supply voltage		1.60		3.6	V
AV_{CC}	Analog supply voltage		1.60		3.6	
T_A	Temperature range		-40		85	°C
T_j	Junction temperature		-40		105	

Table 32-68. Accuracy Characteristics

Symbol	Parameter	Condition [2]		Min.	Typ.	Max.	Units
RES	Resolution	12-bit resolution	Differential	8	12	12	Bits
			Single ended signed	7	11	11	
			Single ended unsigned	8	12	12	
INL [1]	Integral non-linearity	Differential mode	16ksps, V_{REF} = 3V		0.5	1	lsb
			16ksps, all V_{REF}		0.8	2	
			300ksps, V_{REF} = 3V		0.6	1	
			300ksps, all V_{REF}		1.0	2	
		Single ended unsigned mode	16ksps, V_{REF} = 3.0V		0.5	1	
			16ksps, all V_{REF}		1.3	2	
DNL [1]	Differential non-linearity	Differential mode	16ksps, V_{REF} = 3V		0.3	1	lsb
			16ksps, all V_{REF}		0.5	1	
			300ksps, V_{REF} = 3V		0.3	1	
			300ksps, all V_{REF}		0.5	1	
		Single ended unsigned mode	16ksps, V_{REF} = 3.0V		0.6	1	
			16ksps, all V_{REF}		0.6	1	
	Offset error	Differential mode	300ksps, V_{REF} = 3V		-7		mV
			Temperature drift, V_{REF} = 3V		0.01		mV/K
			Operating voltage drift		0.16		mV/V
	Gain error	Differential mode	External reference		-5		mV
			AV_{CC}/1.6		-5		
			AV_{CC}/2.0		-6		
			Bandgap		±10		
			Temperature drift		0.02		mV/K
			Operating voltage drift		2		mV/V
	Gain error	Single ended unsigned mode	External reference		-8		mV
			AV_{CC}/1.6		-8		
			AV_{CC}/2.0		-8		
			Bandgap		±10		
			Temperature drift		0.03		mV/K
			Operating voltage drift		2		mV/V

Notes:
1. Maximum numbers are based on characterization and not tested in production and valid for 5% to 95% input voltage range.
2. Unless otherwise noted all linearity, offset and gain error numbers are valid under the condition that external V_{REF} is used.

Symbol	Parameter	Condition		Min.	Typ.	Max.	Units
R_Q	Negative impedance [1]	XOSCPWR=0, FRQRANGE=0	0.4MHz resonator, CL=100pF		44k		Ω
			1MHz crystal, CL=20pF		67k		
			2MHz crystal, CL=20pF		67k		
		XOSCPWR=0, FRQRANGE=1, CL=20pF	2MHz crystal		82k		
			8MHz crystal		1500		
			9MHz crystal		1500		
		XOSCPWR=0, FRQRANGE=2, CL=20pF	8MHz crystal		2700		
			9MHz crystal		2700		
			12MHz crystal		1000		
		XOSCPWR=0, FRQRANGE=3, CL=20pF	9MHz crystal		3600		
			12MHz crystal		1300		
			16MHz crystal		590		
		XOSCPWR=1, FRQRANGE=0, CL=20pF	9MHz crystal		390		
			12MHz crystal		50		
			16MHz crystal		10		
		XOSCPWR=1, FRQRANGE=1, CL=20pF	9MHz crystal		1500		
			12MHz crystal		650		
			16MHz crystal		270		
		XOSCPWR=1, FRQRANGE=2, CL=20pF	12MHz crystal		1000		
			16MHz crystal		440		
		XOSCPWR=1, FRQRANGE=3, CL=20pF	12MHz crystal		1300		
			16MHz crystal		590		
	ESR	SF = safety factor				min(R_Q)/SF	kΩ
	Start-up time	XOSCPWR=0, FRQRANGE=0	0.4MHz resonator, CL=100pF		1.0		ms
		XOSCPWR=0, FRQRANGE=1	2MHz resonator, CL=20pF		2.6		
		XOSCPWR=0, FRQRANGE=2	8MHz resonator, CL=20pF		0.8		
		XOSCPWR=0, FRQRANGE=3	12MHz resonator, CL=20pF		1.0		
		XOSCPWR=1, FRQRANGE=3	16MHz resonator, CL=20pF		1.4		

Table 32-150. Current Consumption for Modules and Peripherals

Symbol	Parameter	Condition [1]		Min.	Typ.	Max.	Units
I_{CC}	ULP oscillator				0.93		µA
	32.768kHz int. oscillator				27		
	2MHz int. oscillator				85		
		DFLL enabled with 32.768kHz int. osc. as reference			115		
	32MHz int. oscillator				240		
		DFLL enabled with 32.768kHz int. osc. as reference			430		
	PLL	20× multiplication factor, 32MHz int. osc. DIV4 as reference			300		
	Watchdog timer				1.0		
	BOD	Continuous mode			140		
		Sampled mode, includes ULP oscillator			1.3		
	Internal 1.0V reference				220		
	Temperature sensor				215		
	ADC	16ksps, V_{REF} = Ext. ref.			1.12		mA
			CURRLIMIT = LOW		1.01		
			CURRLIMIT = MEDIUM		0.9		
			CURRLIMIT = HIGH		0.8		
		75ksps, V_{REF} = Ext. ref.	CURRLIMIT = LOW		1.7		
		300ksps, V_{REF} = Ext. ref.			3.1		
	USART	Rx and Tx enabled, 9600 BAUD			9.5		µA
	Flash memory and EEPROM programming				4.0		mA

Note: 1. All parameters measured as the difference in current consumption between module enabled and disabled. All data at V_{CC} = 3.0V, Clk_{SYS} = 1MHz external clock without prescaling, T = 25°C unless other conditions are given.

32.6.5 I/O Pin Characteristics

The I/O pins complies with the JEDEC LVTTL and LVCMOS specification and the high- and low level input and output voltage limits reflect or exceed this specification.

Table 32-152. I/O Pin Characteristics

Symbol	Parameter	Condition		Min.	Typ.	Max.	Units
I_{OH} (1)/ I_{OL} (2)	I/O pin source/sink current			-15		15	mA
V_{IH}	High level input voltage	V_{CC} = 2.4 - 3.6V		0.7 * V_{CC}		V_{CC} + 0.5	V
		V_{CC} = 1.6 - 2.4V		0.8 * V_{CC}		V_{CC} + 0.5	
V_{IL}	Low level input voltage	V_{CC} = 2.4 - 3.6V		-0.5		0.3 * V_{CC}	
		V_{CC} = 1.6 - 2.4V		-0.5		0.2 * V_{CC}	
V_{OH}	High level output voltage	V_{CC} = 3.3V	I_{OH} = -4mA	2.6	2.9		
		V_{CC} = 3.0V	I_{OH} = -3mA	2.1	2.6		
		V_{CC} = 1.8V	I_{OH} = -1mA	1.4	1.6		
V_{OL}	Low level output voltage	V_{CC} = 3.3V	I_{OL} = 8mA		0.4	0.76	
		V_{CC} = 3.0V	I_{OL} = 5mA		0.3	0.64	
		V_{CC} = 1.8V	I_{OL} = 3mA		0.2	0.46	
I_{IN}	Input leakage current I/O pin	T = 25°C			<0.01	1	µA
R_P	Pull/buss keeper resistor				25		kΩ

Notes:
1. The sum of all I_{OH} for PORTA and PORTB must not exceed 100mA.
   The sum of all I_{OH} for PORTC, PORTD, and PORTE must for each port not exceed 200mA.
   The sum of all I_{OH} for pins PF[0-5] on PORTF must not exceed 200mA.
   The sum of all I_{OL} for pins PF[6-7] on PORTF, PORTR, and PDI must not exceed 100mA.
2. The sum of all I_{OL} for PORTA and PORTB must not exceed 100mA.
   The sum of all I_{OL} for PORTC, PORTD, and PORTE must for each port not exceed 200mA.
   The sum of all I_{OL} for pins PF[0-5] on PORTF must not exceed 200mA.
   The sum of all I_{OL} for pins PF[6-7] on PORTF, PORTR, and PDI must not exceed 100mA.

32.6.6 ADC Characteristics

Table 32-153. Power Supply, Reference, and Input Range

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
AV_{CC}	Analog supply voltage		V_{CC} - 0.3		V_{CC} + 0.3	V
V_{REF}	Reference voltage		1		AV_{CC} - 0.6	
R_{in}	Input resistance	Switched			4.5	kΩ
C_{in}	Input capacitance	Switched			5	pF
R_{AREF}	Reference input resistance	(leakage only)		>10		MΩ
C_{AREF}	Reference input capacitance	Static load		7		pF

Table 32-170.External Clock with Prescaler [1] for System Clock

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
$1/t_{CK}$	Clock Frequency [2]	V_{CC} = 1.6 - 1.8V	0		90	MHz
		V_{CC} = 2.7 - 3.6V	0		142	
t_{CK}	Clock Period	V_{CC} = 1.6 - 1.8V	11			ns
		V_{CC} = 2.7 - 3.6V	7			
t_{CH}	Clock High Time	V_{CC} = 1.6 - 1.8V	4.5			
		V_{CC} = 2.7 - 3.6V	2.4			
t_{CL}	Clock Low Time	V_{CC} = 1.6 - 1.8V	4.5			
		V_{CC} = 2.7 - 3.6V	2.4			
t_{CR}	Rise Time (for maximum frequency)	V_{CC} = 1.6 - 1.8V			1.5	
		V_{CC} = 2.7 - 3.6V			1.0	
t_{CF}	Fall Time (for maximum frequency)	V_{CC} = 1.6 - 1.8V			1.5	
		V_{CC} = 2.7 - 3.6V			1.0	
Δt_{CK}	Change in period from one clock cycle to the next				10	%

Notes:
1. System Clock Prescalers must be set so that maximum CPU clock frequency for device is not exceeded.
2. The maximum frequency vs. supply voltage is linear between 1.6V and 2.7V, and the same applies for all other parameters with supply voltage conditions.

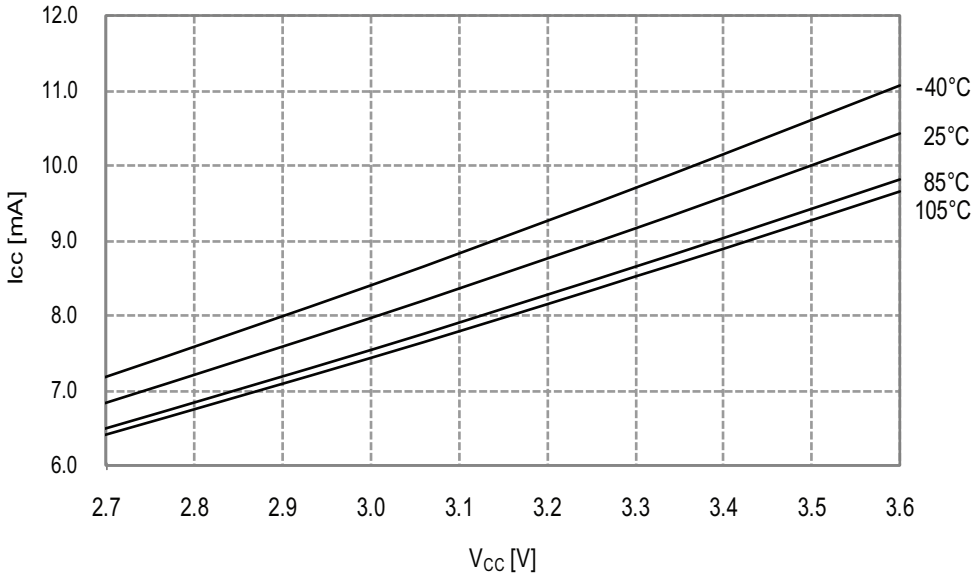
32.6.13.7 External 16MHz Crystal Oscillator and XOSC Characteristics

Table 32-171. External 16MHz Crystal Oscillator and XOSC Characteristics

Symbol	Parameter	Condition		Min.	Typ.	Max.	Units
	Cycle to cycle jitter	XOSCPWR=0	FRQRANGE=0		0		ns
			FRQRANGE=1, 2, or 3		0		
		XOSCPWR=1			0		
	Long term jitter	XOSCPWR=0	FRQRANGE=0		0		
			FRQRANGE=1, 2, or 3		0		
		XOSCPWR=1			0		
	Frequency error	XOSCPWR=0	FRQRANGE=0		0.03		%
			FRQRANGE=1		0.03		
			FRQRANGE=2 or 3		0.03		
		XOSCPWR=1			0.003		
	Duty cycle	XOSCPWR=0	FRQRANGE=0		50		%
			FRQRANGE=1		50		
			FRQRANGE=2 or 3		50		
		XOSCPWR=1			50		

Figure 33-7. Active Mode Supply Current vs. V_{CC}

f_{SYS} = 32MHz internal oscillator



33.1.1.2 Idle Mode Supply Current

Figure 33-8. Idle Mode Supply Current vs. Frequency

f_{SYS} = 0 - 1MHz external clock, T = 25°C

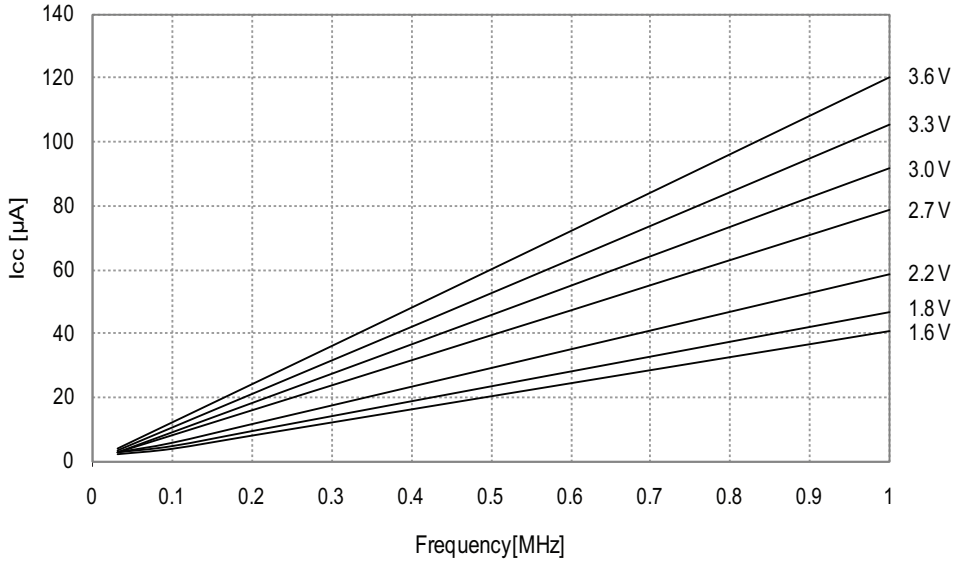


Figure 33-63. 32MHz Internal Oscillator CALA Calibration Step Size

T = 25°C, V_{CC} = 3.0V

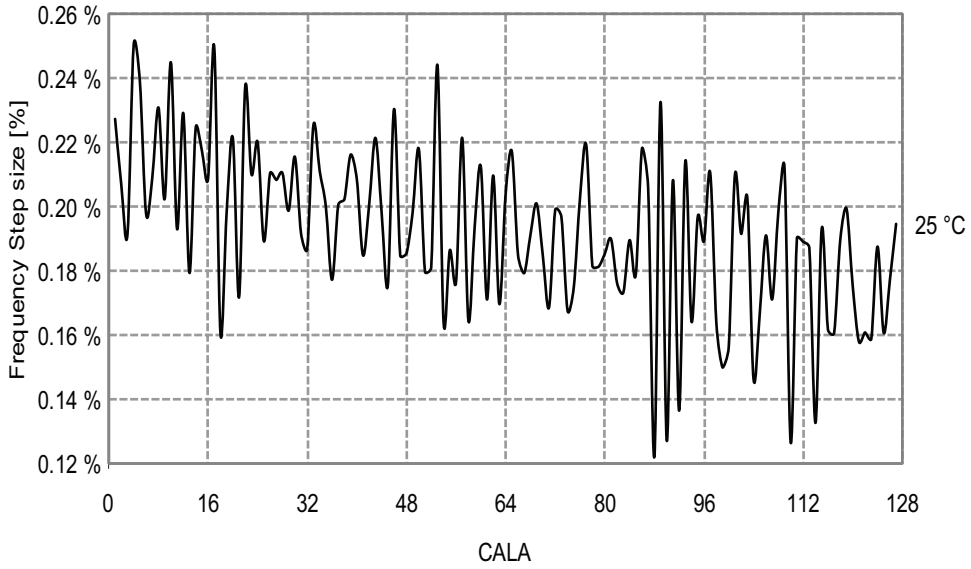
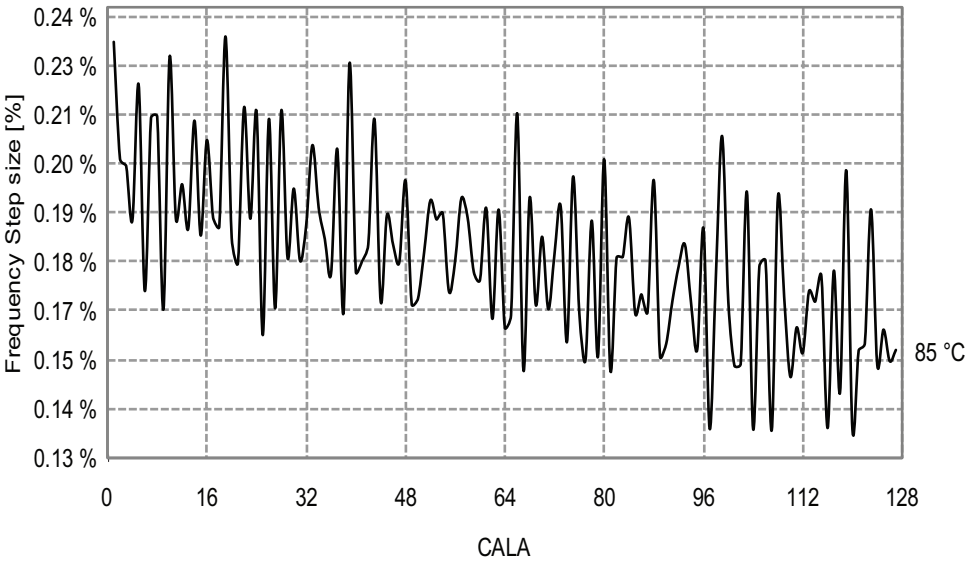


Figure 33-64. 32MHz Internal Oscillator CALA Calibration Step Size

T = 85°C, V_{CC} = 3.0V



33.1.9 Two-Wire Interface Characteristics

Figure 33-69. SDA Hold Time vs. Temperature

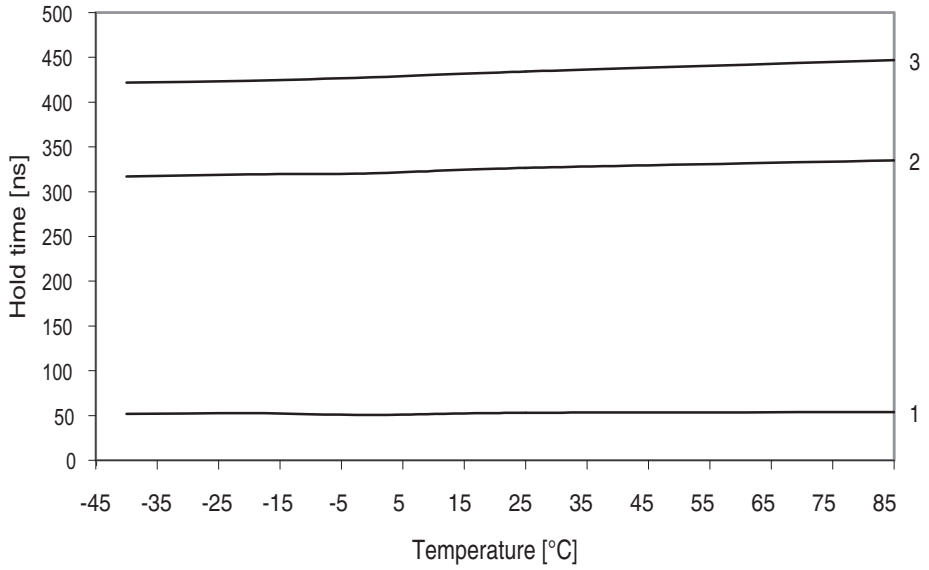


Figure 33-70. SDA Hold Time vs. Supply Voltage

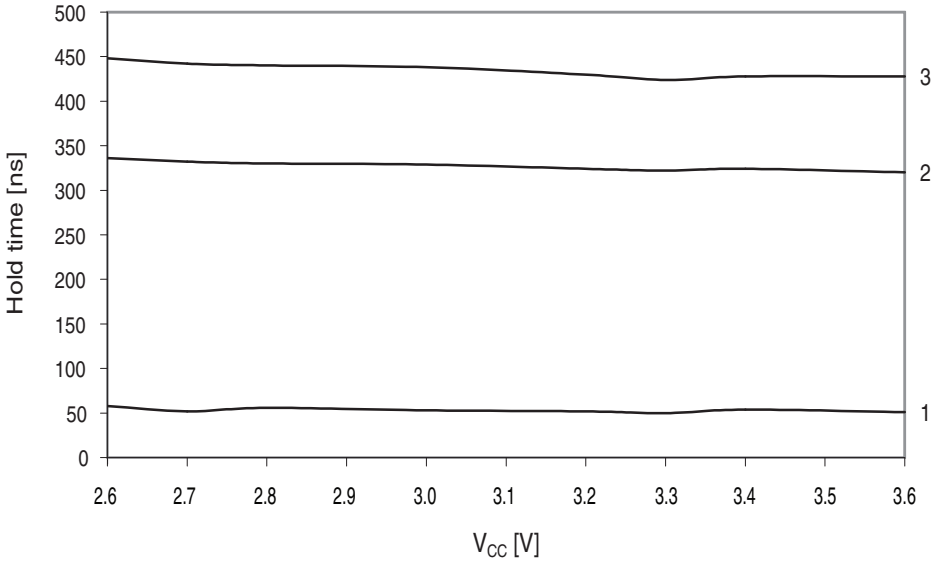


Figure 33-167. I/O Pin Output Voltage vs. Sink Current

V_{CC} = 3.0V

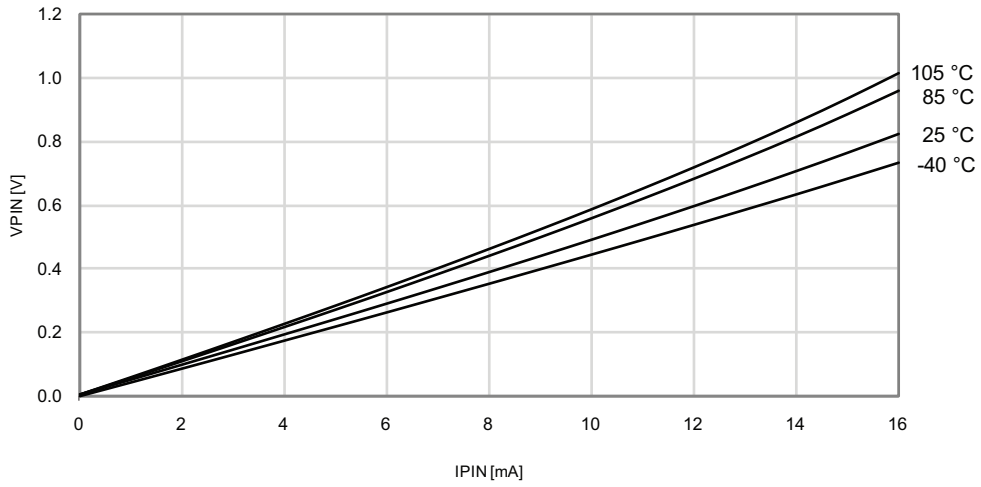


Figure 33-168. I/O Pin Output Voltage vs. Sink Current

V_{CC} = 3.3V

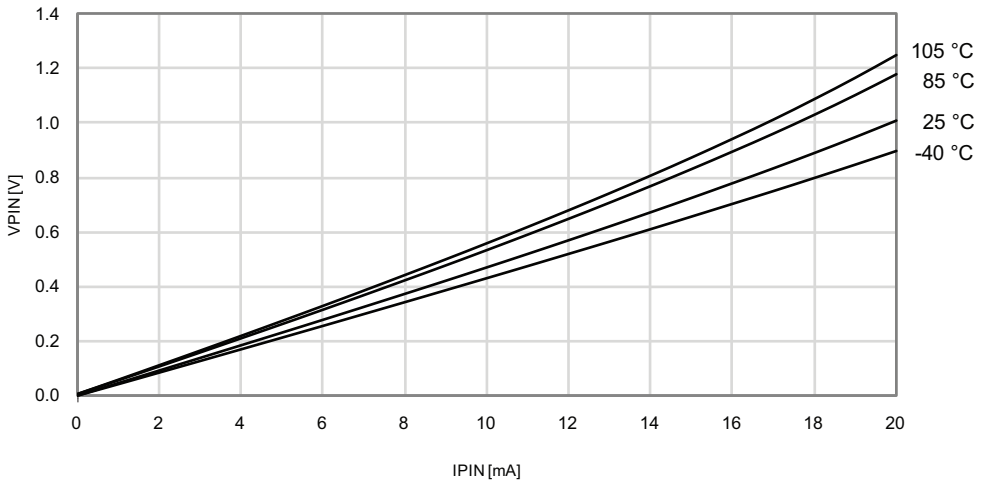


Figure 33-245.DNL Error vs. External V_{REF}

T = 25°C, V_{CC} = 3.6V, external reference

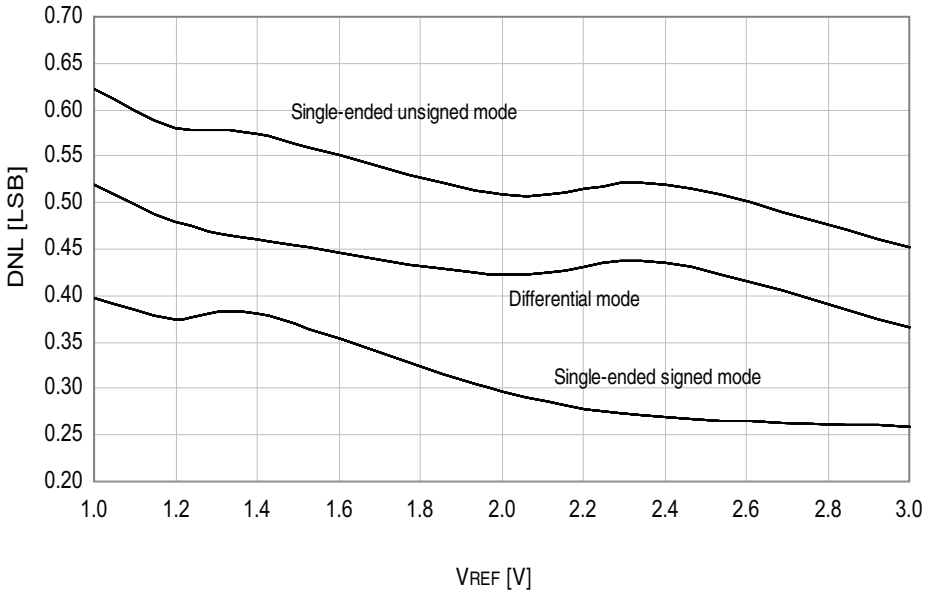


Figure 33-246.DNL Error vs. Sample Rate

T = 25°C, V_{CC} = 3.6V, V_{REF} = 3.0V external

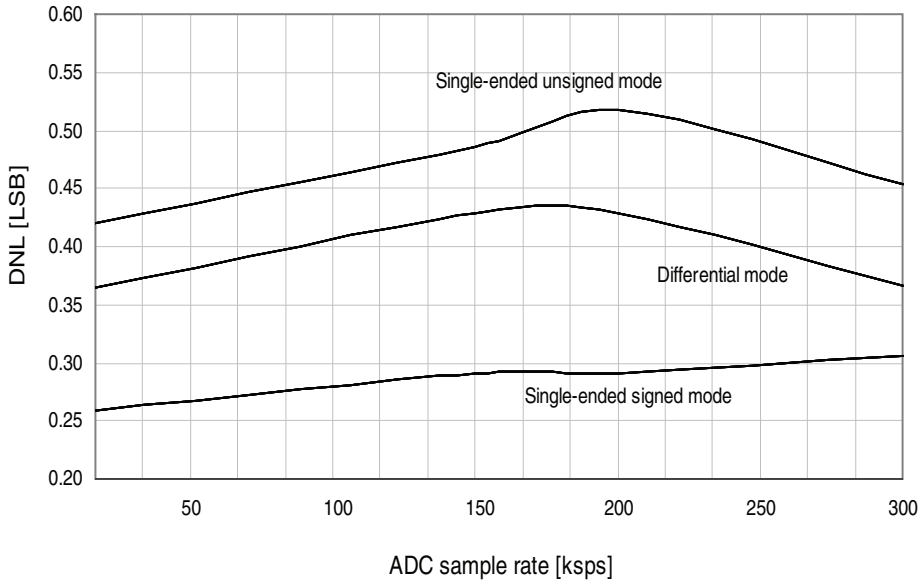


Figure 33-247.DNL Error vs. Input Code

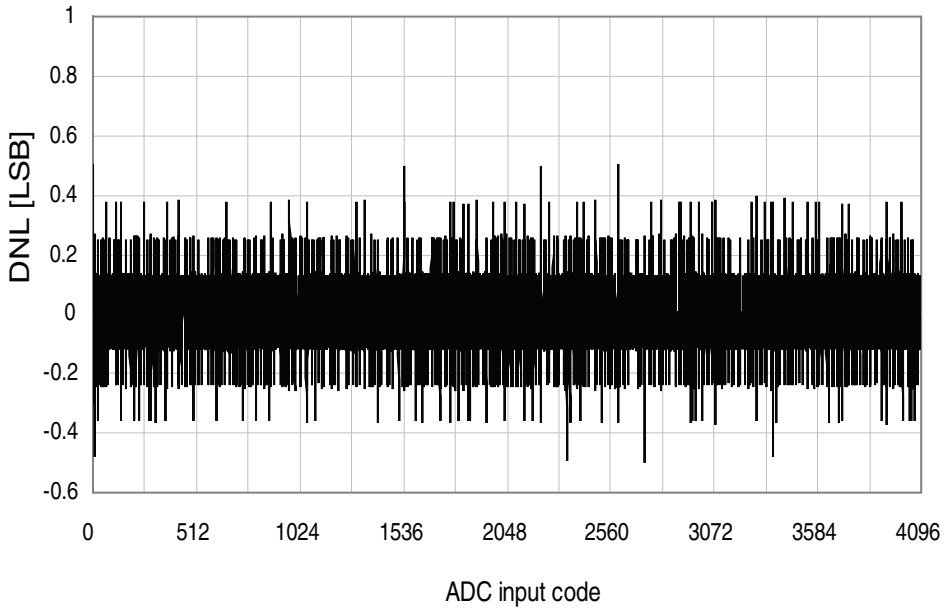


Figure 33-248.Gain Error vs. V_{REF}

T = 25°C, V_{CC} = 3.6V, ADC sample rate = 300ksps

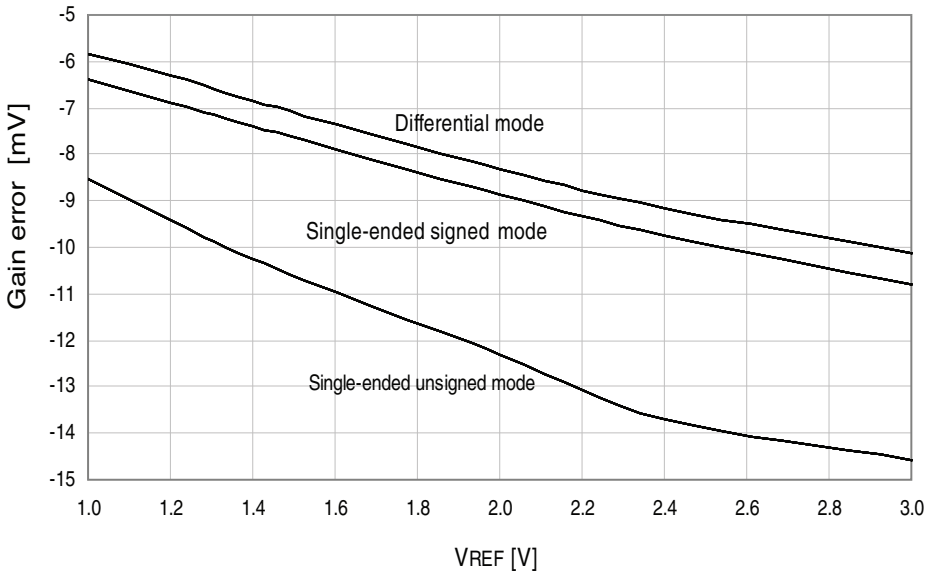


Figure 33-291.Idle Mode Supply Current vs. Frequency

f_{SYS} = 1 - 32MHz external clock, T = 25°C

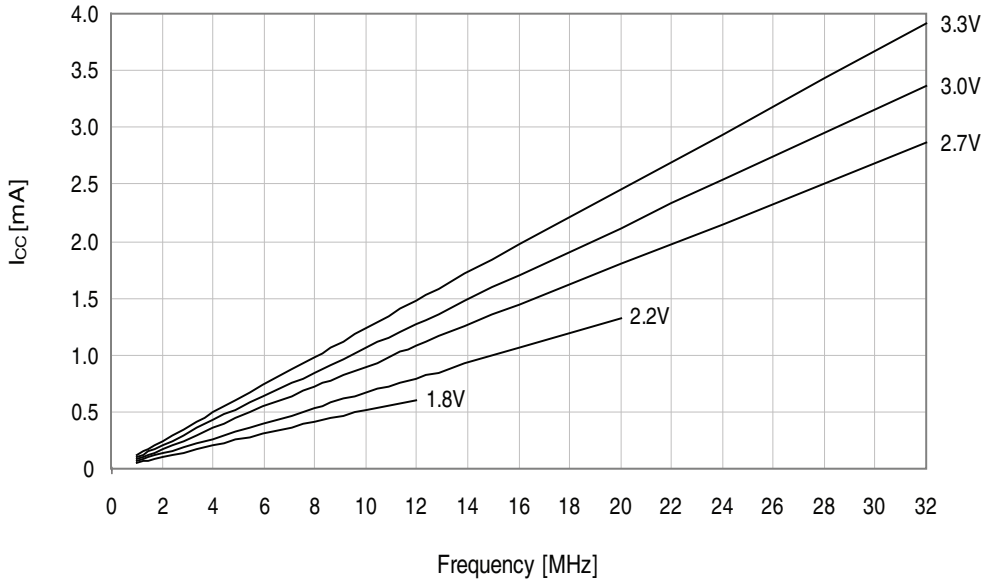


Figure 33-292.Idle Mode Supply Current vs. V_{CC}

f_{SYS} = 32.768kHz internal oscillator

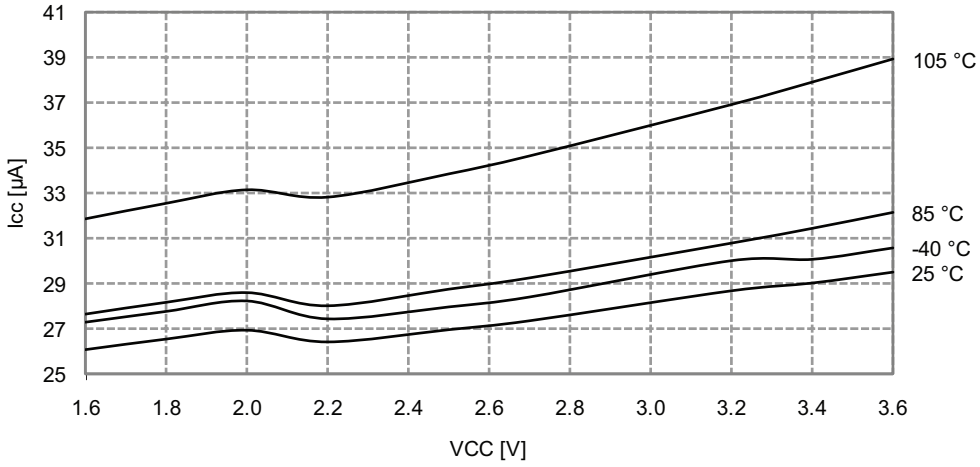
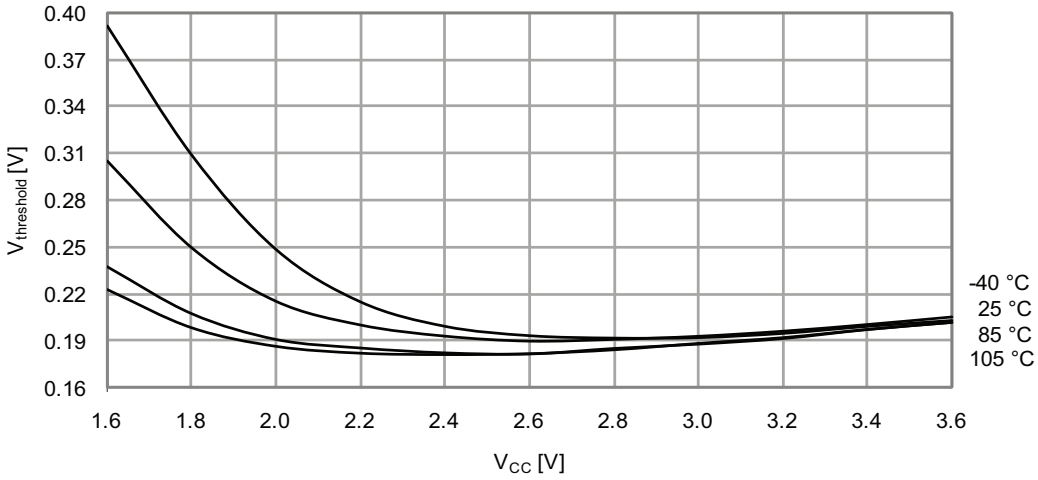


Figure 33-311.I/O Pin Input Hysteresis vs. V_{CC}



33.5.3 ADC Characteristics

Figure 33-312.INL Error vs. External V_{REF}

T = 25°C, V_{CC} = 3.6V, external reference

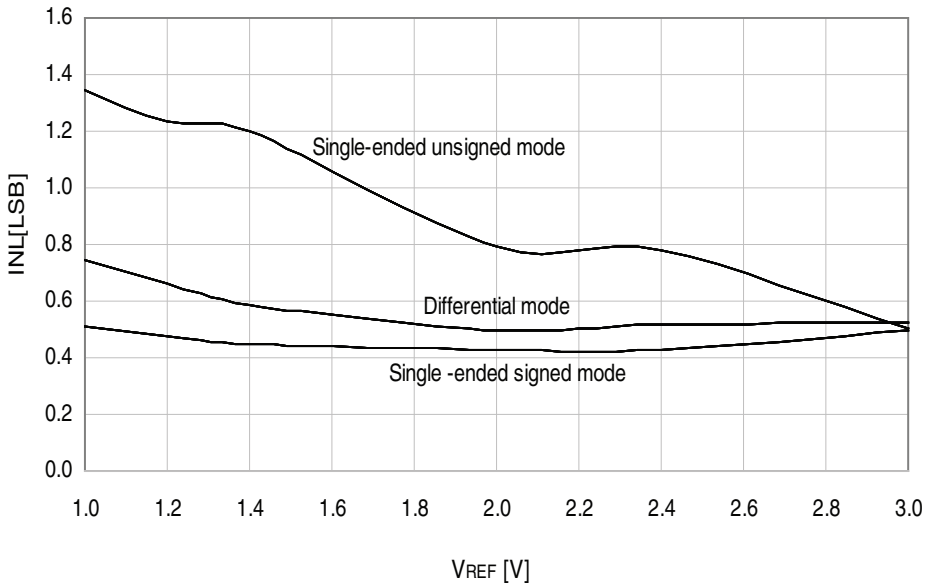


Figure 33-325. Analog Comparator Current Source vs. Calibration Value

V_{CC} = 3.0V

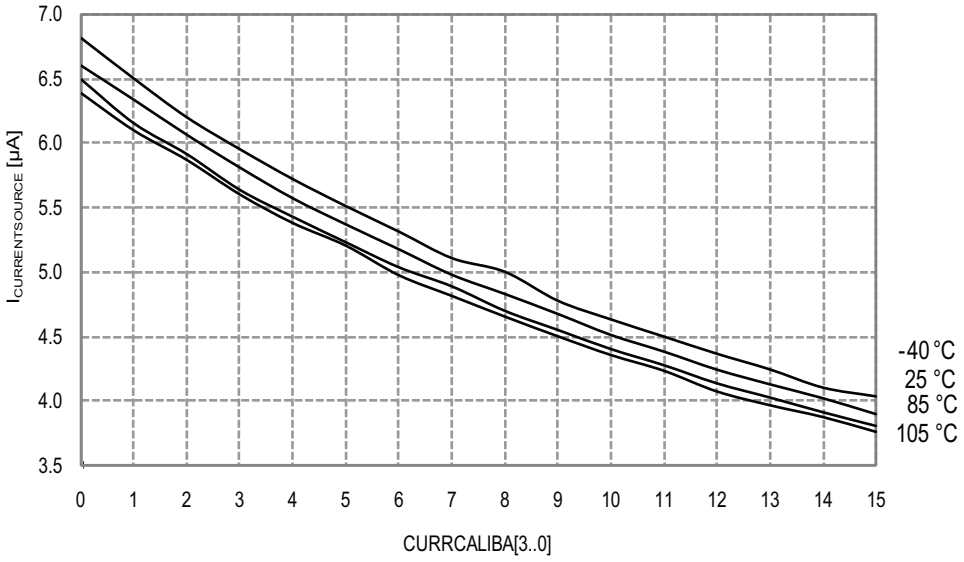


Figure 33-326. Voltage Scaler INL vs. SCALEFAC

T = 25°C, V_{CC} = 3.0V

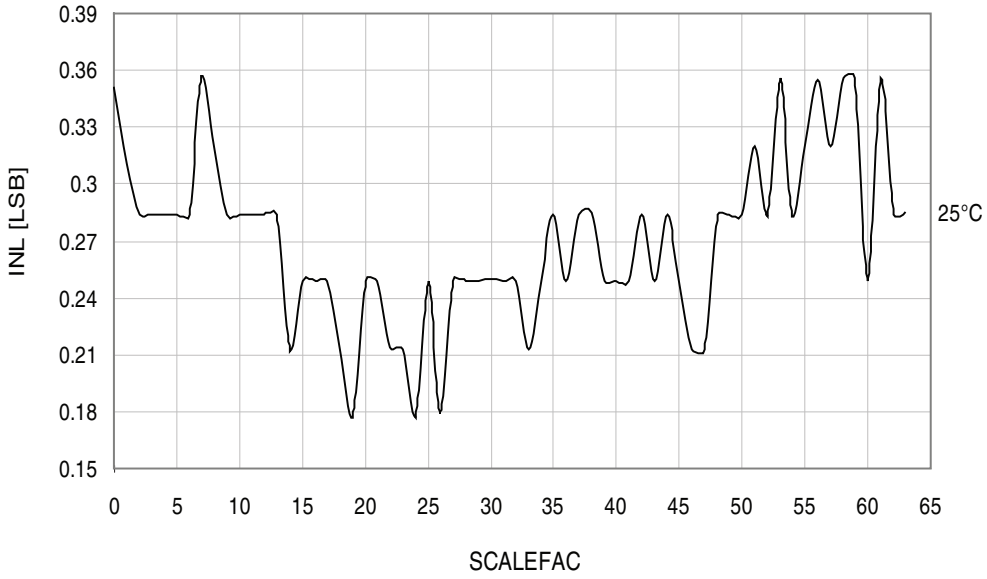
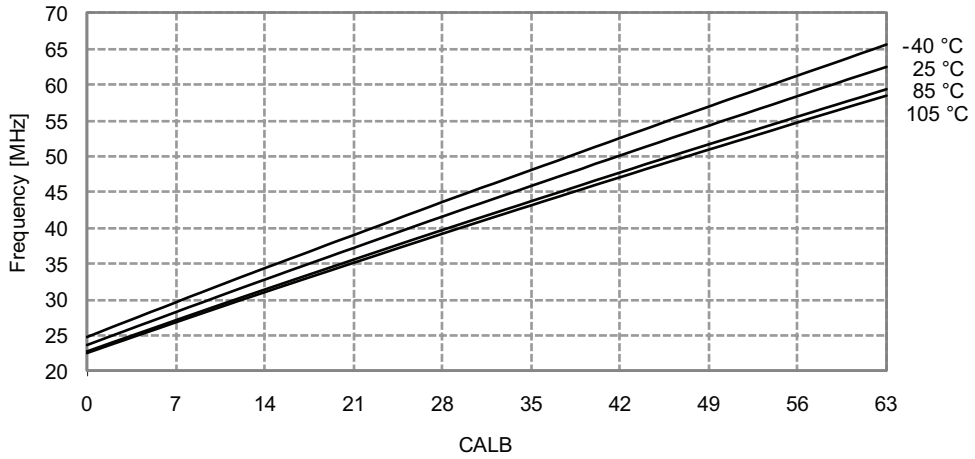


Figure 33-347. 32MHz Internal Oscillator Frequency vs. CALB Calibration Value

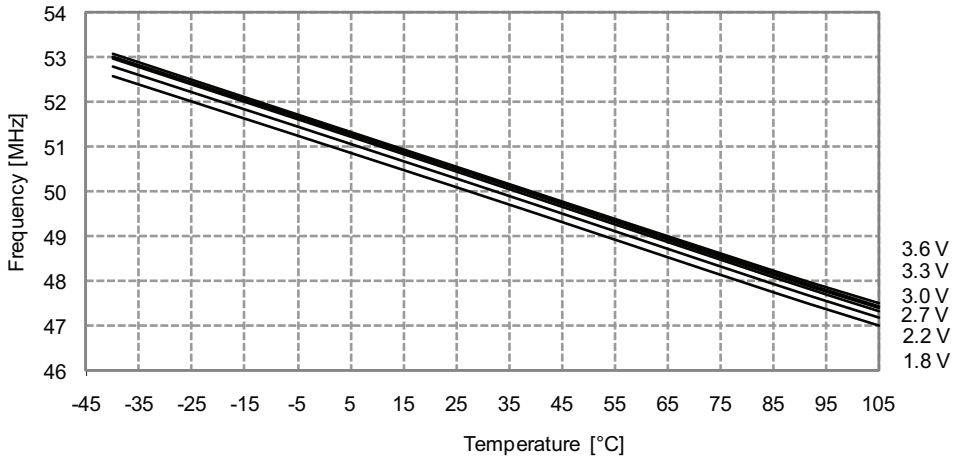
V_{CC} = 3.0V



33.5.8.5 32MHz Internal Oscillator Calibrated to 48MHz

Figure 33-348. 48MHz Internal Oscillator Frequency vs. Temperature

DFLL disabled



- 1× gain: 2.4 V
- 2× gain: 1.2 V
- 4× gain: 0.6 V
- 8× gain: 300 mV
- 16× gain: 150 mV
- 32× gain: 75 mV
- 64× gain: 38 mV

Problem fix/workaround

Keep the amplified voltage output from the ADC gain stage below 2.4V in order to get a correct result, or keep ADC voltage reference below 2.4V.

6. ADC Event on compare match non-functional

ADC signalling event will be given at every conversion complete even if Interrupt mode (INTMODE) is set to BELOW or ABOVE.

Problem fix/workaround

Enable and use interrupt on compare match when using the compare function.

7. ADC propagation delay is not correct when 8× – 64× gain is used

The propagation delay will increase by only one ADC clock cycle for all gain settings.

Problem fix/workaround

None.

8. Bandgap measurement with the ADC is non-functional when V_{CC} is below 2.7V

The ADC can not be used to do bandgap measurements when V_{CC} is below 2.7V.

Problem fix/workaround

None.

9. Accuracy lost on first three samples after switching input to ADC gain stage

Due to memory effect in the ADC gain stage, the first three samples after changing input channel must be disregarded to achieve 12-bit accuracy.

Problem fix/workaround

Run three ADC conversions and discard these results after changing input channels to ADC gain stage.

10. Configuration of PGM and CWCM not as described in XMEGA D Manual

Enabling Common Waveform Channel Mode will enable Pattern generation mode (PGM), but not Common Waveform Channel Mode.

Enabling Pattern Generation Mode (PGM) and not Common Waveform Channel Mode (CWCM) will enable both Pattern Generation Mode and Common Waveform Channel Mode.

16. NMI Flag for Crystal Oscillator Failure automatically cleared

NMI flag for Crystal Oscillator Failure (XOSCFDIF) will be automatically cleared when executing the NMI interrupt handler.

Problem fix/workaround

This device revision has only one NMI interrupt source, so checking the interrupt source in software is not required.

17. Writing EEPROM or Flash while reading any of them will not work

The EEPROM and Flash cannot be written while reading EEPROM or Flash, or while executing code in Active mode.

Problem fix/workaround

Enter IDLE sleep mode within 2.5µs (five 2MHz clock cycles and 80 32MHz clock cycles) after starting an EEPROM or flash write operation. Wake-up source must either be EEPROM ready or NVM ready interrupt. Alternatively set up a Timer/Counter to give an overflow interrupt 7ms after the erase or write operation has started, or 13ms after atomic erase-and-write operation has started, and then enter IDLE sleep mode.

18. RTC Counter value not correctly read after sleep

If the RTC is set to wake up the device on RTC Overflow and bit 0 of RTC CNT is identical to bit 0 of RTC PER as the device is entering sleep, the value in the RTC count register can not be read correctly within the first prescaled RTC clock cycle after wake-up. The value read will be the same as the value in the register when entering sleep.

The same applies if RTC Compare Match is used as wake-up source.

Problem fix/workaround

Wait at least one prescaled RTC clock cycle before reading the RTC CNT value.

19. Pending asynchronous RTC-interrupts will not wake up device

Asynchronous Interrupts from the Real-Time-Counter that is pending when the sleep instruction is executed, will be ignored until the device is woken from another source or the source triggers again.

Problem fix/workaround

None.

20. TWI Transmit collision flag not cleared on repeated start

The TWI transmit collision flag should be automatically cleared on start and repeated start, but is only cleared on start.

Problem fix/workaround

Clear the flag in software after address interrupt.

21. Clearing TWI Stop Interrupt Flag may lock the bus

If software clears the STOP Interrupt Flag (APIF) on the same Peripheral Clock cycle as the hardware sets this flag due to a new address received, CLKHOLD is not cleared and the SCL line is not released. This will lock the bus.

34.6 Atmel ATxmega384D3

34.6.1 Rev. B

- Sampled BOD in Active mode will cause noise when bandgap is used as reference
- Temperature sensor not calibrated

1. Sampled BOD in Active mode will cause noise when bandgap is used as reference

Using the BOD in sampled mode when the device is running in Active or Idle mode will add noise on the bandgap reference for ADC, DAC and Analog Comparator.

Problem fix/workaround

If the bandgap is used as reference for either the ADC, DAC and Analog Comparator, the BOD must not be set in sampled mode.

2. Temperature sensor not calibrated

Temperature sensor factory calibration not implemented.

Problem fix/workaround

None.

34.6.2 Rev. A

Not sampled.